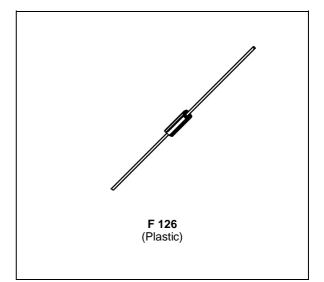


BYT 11-600 \rightarrow 1000

FAST RECOVERY RECTIFIER DIODES

- SOFT RECOVERY
- VERY HIGH VOLTAGE
- SMALL RECOVERY CHARGE



APPLICATIONS

- ANTISATURATION DIODES FOR TRANSIS-TOR BASE DRIVE
- SNUBBER DIODES

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit		
I _{FRM}	Repetive Peak Forward Current	20	А		
I _{F (AV)}	Average Forward Current *	1	A		
I _{FSM}	Surge non Repetitive Forward Current	35	A		
P _{tot}	Power Dissipation *	1.25	W		
T _{stg} Tj	Storage and Junction Temperature Range	- 55 to + 150 - 55 to + 150	°C		
TL	Maximum Lead Temperature for Soldering during 10s at 4mm230from Case				

Symbol	Parameter		Unit			
	i arameter	600	800	1000	onic	
V _{RR}	М	Repetitive Peak Reverse Voltage	600	800	1000	V

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R _{th (j} - a)	Junction-ambient*	60	°C/W

* On infinite heatsink with 10mm lead length.

November 1994

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Synbol		Min.	Тур.	Max.	Unit		
I _R	T _j = 25°C	$V_R = V_{RRM}$				20	μΑ
VF	T _j = 25°C	I _F = 1A				1.3	V

RECOVERY CHARACTERISTICS

Symbol		Test	Min.	Тур.	Max.	Unit		
t _{rr}	T _j = 25°C	I _F = 0.5A	I _R = 1A	I _{rr} = 0.25A			100	ns

To evaluate the conduction losses use the following equations:

 $V_F = 1.1 + 0.075 \ I_F \qquad \qquad P = 1.1 \ x \ I_{F(AV)} + 0.075 \ I_{F}^{2}_{(RMS)}$



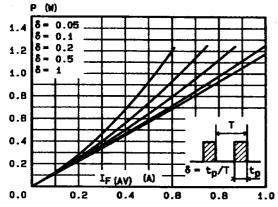


Figure 3. Thermal resistance versus lead length.

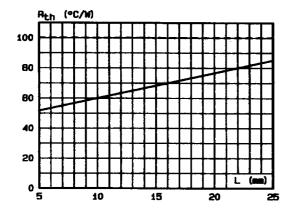
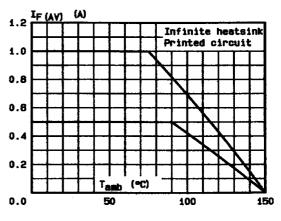
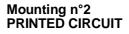
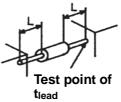


Figure 2. Average forward current versus ambient temperature.



Mounting n°1 INFINITE HEATSINK







SGS-THOMSON

Figure 4. Transient thermal impedance junction-ambient for mounting n^2 versus pulse duration (L = 10 mm).

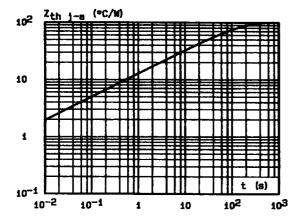


Figure 6. Capacitance versus	reverse applied
voltage	

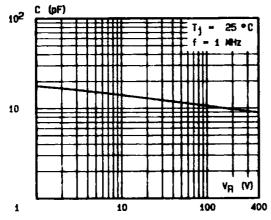


Figure 5. Peak forward current versus peak forward voltage drop (maximum values).

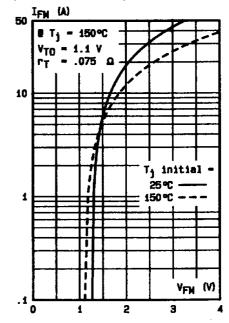
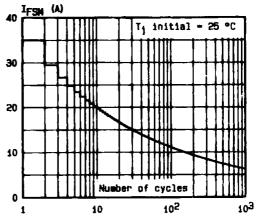
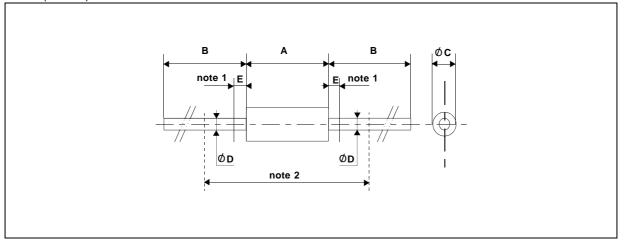


Figure 7. Non repetitive surge peak current versus number of cycles



PACKAGE MECHANICAL DATA

F 126 (Plastic)



		DIMEN	SIONS		
REF.	. Millimeters		Inches		NOTES
	Min.	Max.	Min.	Max.	
А	6.05	6.35	0.238	0.250	1 - The lead diameter \varnothing D is not controlled over zone E
В	26		1.024		
ØC	2.95	3.05	0.116	0.120	2 - The minimum axial lengh within which the device may be placed with its leads bent at right angles is 0.59"(15 mm)
ØD	0.76	0.86	0.029	0.034	placed with its leads bent at right angles is 0.55 (15 min)
Е		1.27		0.050	

Cooling method: by convection (method A) Marking: type number ring at cathode end Weight: 0.4g

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsability for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics or systems without express written approval of SGS-THOMSON Microelectronics.

© 1994 SGS-THOMSON Microelectronics - Printed in Italy - All rights reserved.

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -Singapore - Spain - Sweden - Switzerland - Taiwan - United Kingdom - U.S.A.





This datasheet has been downloaded from:

www.EEworld.com.cn

Free Download Daily Updated Database 100% Free Datasheet Search Site 100% Free IC Replacement Search Site Convenient Electronic Dictionary Fast Search System www.EEworld.com.cn

All Datasheets Cannot Be Modified Without Permission

Copyright © Each Manufacturing Company